



TAYCHIPST

HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

BYW98-200

200V 3.0A

**FEATURES**

- VERY LOW CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIMES

052(1.3)  
048(1.2) DIA1.0(25.4)  
MIN.375(9.5)  
.335(8.5)1.0(25.4)  
MIN.220(5.6)  
.197(5.0) DIA

DO-27

Dimensions in inches and (millimeters)

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS****ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage		200	V
I <sub>FRM</sub>	Repetitive peak forward current *	t <sub>p</sub> =5 μs F=1KHz	110	A
I <sub>F</sub> (AV)	Average forward current*	T <sub>a</sub> = 75°C δ = 0.5	3	A
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10ms Sinusoidal	70	A
T <sub>stg</sub>	Storage temperature range	- 65 to + 150		°C
T <sub>j</sub>	Maximum operating junction temperature	150		°C
T <sub>L</sub>	Maximum lead temperature for soldering during 10s at 4mm from case	230		°C

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	Reverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			10	μA
		T <sub>j</sub> = 100°C				0.5	mA
V <sub>F</sub> **	Forward voltage drop	T <sub>j</sub> = 25°C	I <sub>F</sub> = 9A			1.2	V
		T <sub>j</sub> = 100°C	I <sub>F</sub> = 3A		0.78	0.85	

**RECOVERY CHARACTERISTICS**

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
t <sub>rr</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A	dI <sub>F</sub> /dt = - 50A/μs			35	ns
Q <sub>rr</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 3A	dI <sub>F</sub> /dt = - 20A/μs		15		nC
t <sub>fr</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 3A	dI <sub>F</sub> /dt = - 50A/μs		20		ns
V <sub>FP</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 3A	dI <sub>F</sub> /dt = - 50A/μs		5		V



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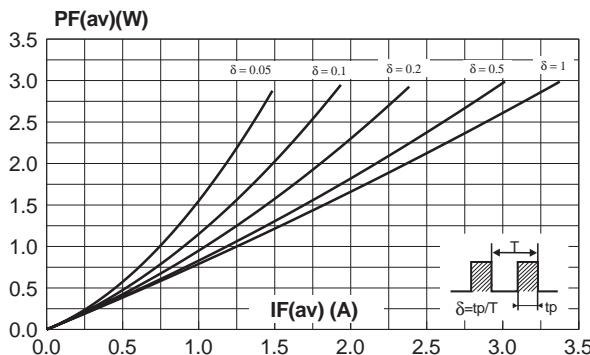
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**BYW98-200**

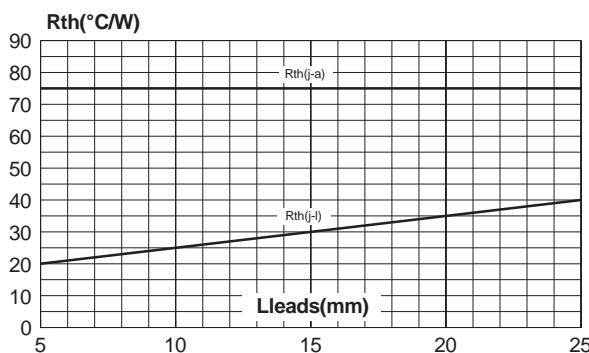
200V 3.0A

## RATINGS AND CHARACTERISTIC CURVES BYW98-200

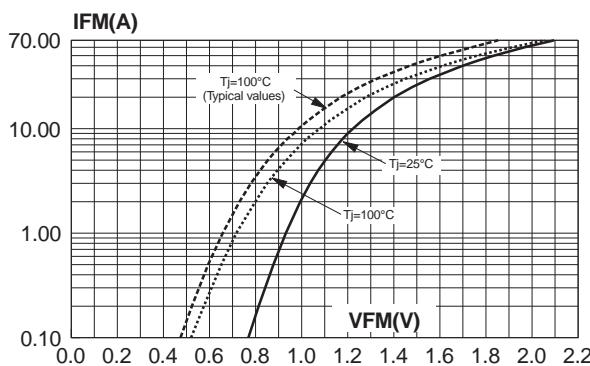
**Fig. 1:** Average forward power dissipation versus average forward current.



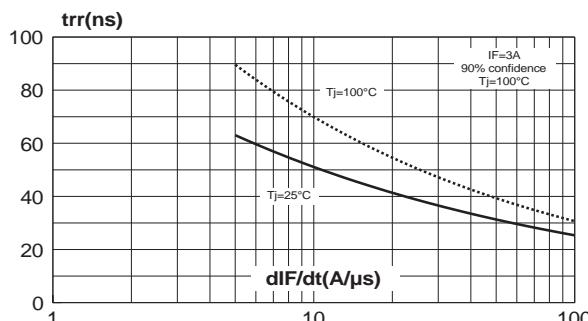
**Fig. 3:** Thermal resistance versus lead length.



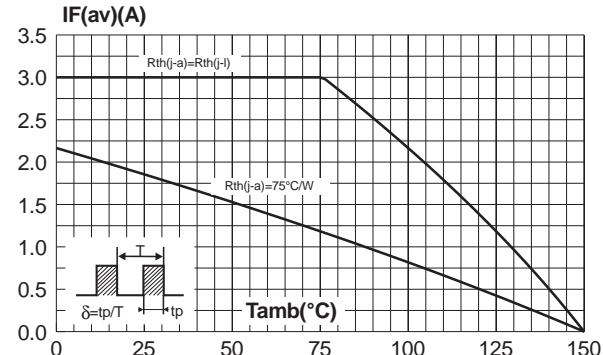
**Fig. 5:** Forward voltage drop versus forward current (maximum values).



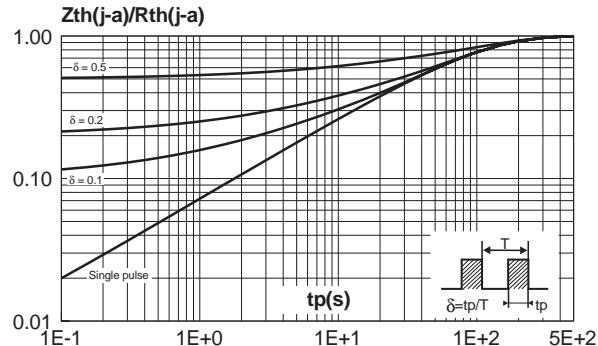
**Fig. 7:** Reverse recovery time versus  $dI_F/dt$ .



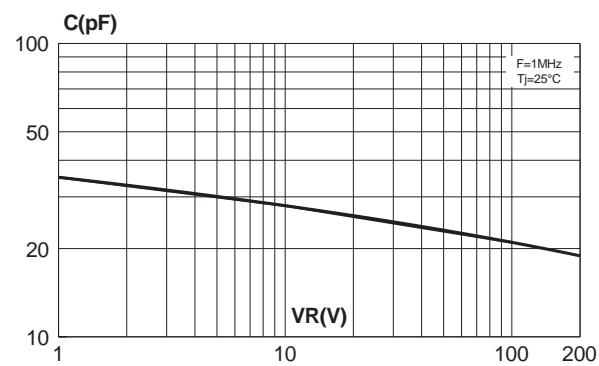
**Fig. 2:** Average forward current versus ambient temperature ( $\delta=0.5$ ).



**Fig. 4:** Variation of thermal impedance junction to ambient versus pulse duration (recommended pad



**Fig. 6:** Junction capacitance versus reverse voltage applied (typical values).



**Fig. 8:** Peak reverse recovery current versus  $dI_F/dt$ .

